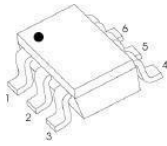
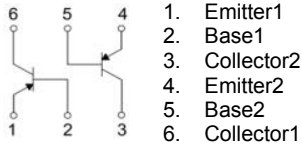


## SOT-363



Marking: 5Ft



## SOT-363 贴片塑封三极管

### SOT-363 Plastic-Encapsulate Transistors

#### 特征 Features

- 一个封装体内集成两个晶体管; Two Transistors in One Package
- 最大功率耗散 200mW; Power Dissipation of 200mW
- 高稳定性和可靠性。High Stability and High Reliability

#### 机械数据 Mechanical Data

- 封装: SOT-363 封装SOT-363 Small Outline Plastic Package
- 环氧树脂UL 易燃等级Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

#### Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-65	V
Emitter -Base Voltage	$V_{EBO}$	-5	V
Collector Current-Continuous	$I_C$	-100	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55-+150	°C
Thermal resistance From junction to ambient	$R_{\theta JA}$	625	°C/W

电特性 (TA = 25°C 除非另有规定)

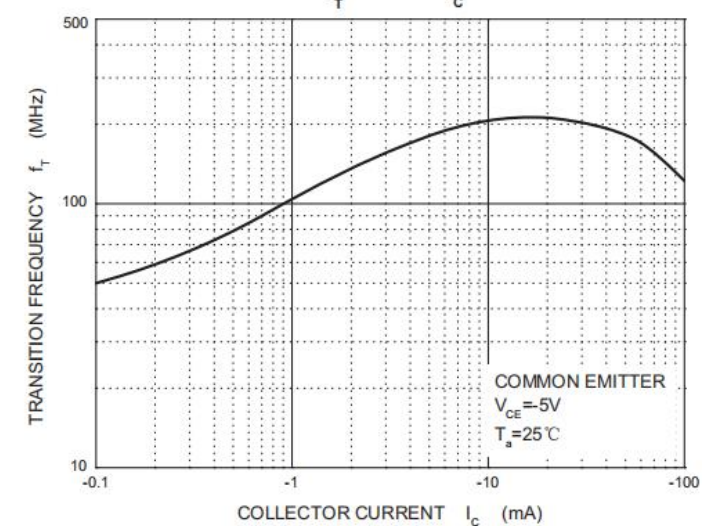
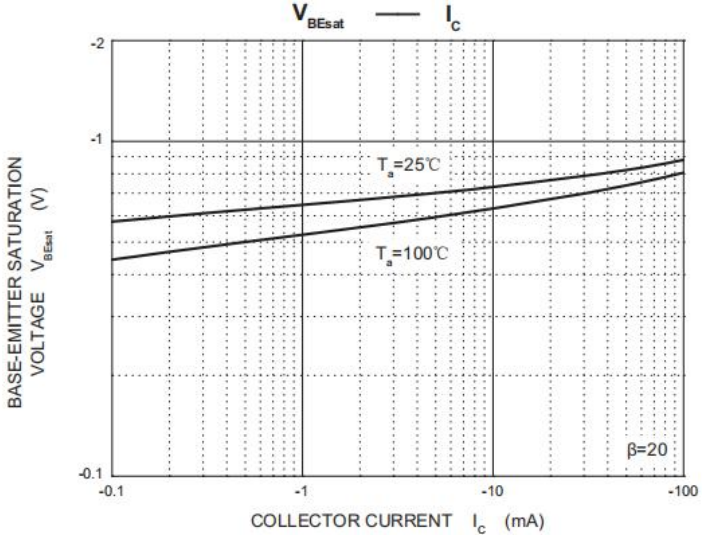
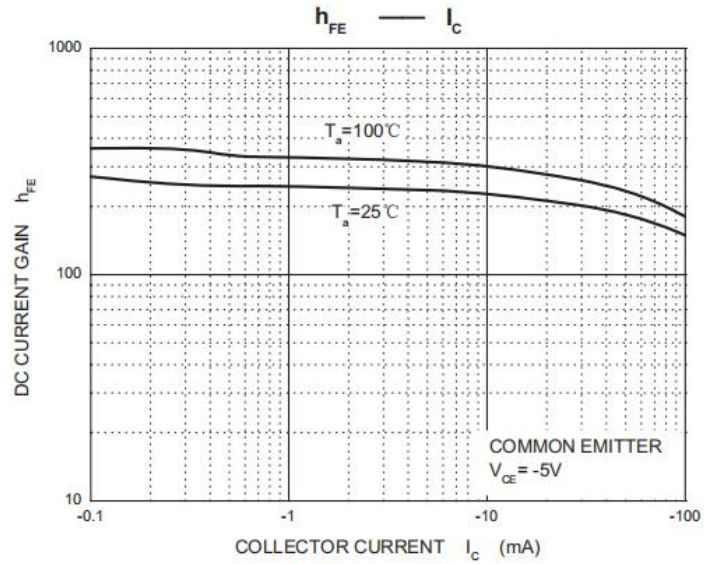
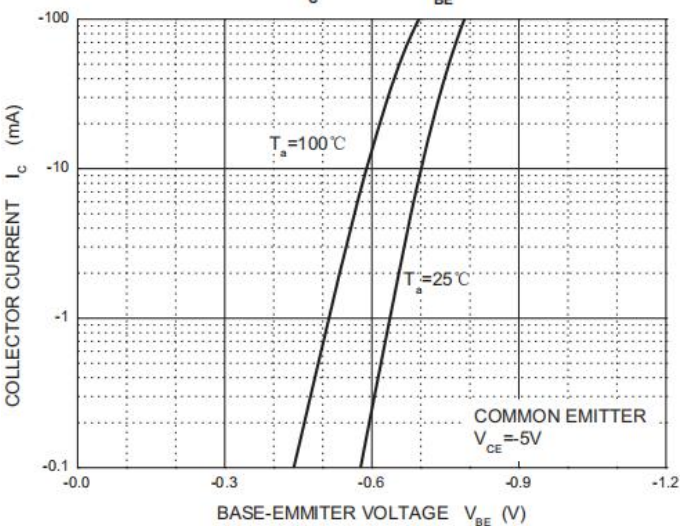
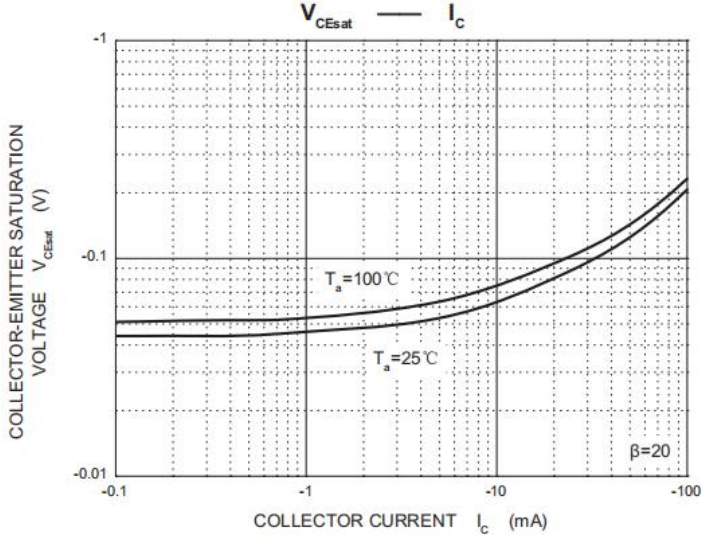
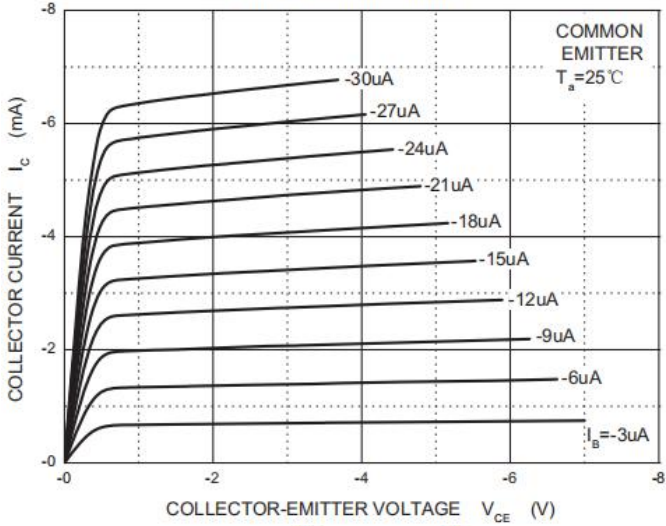
#### Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

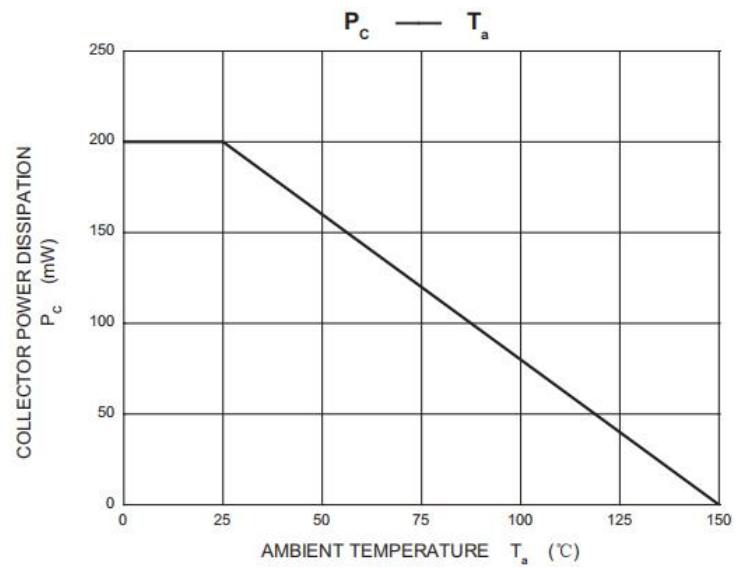
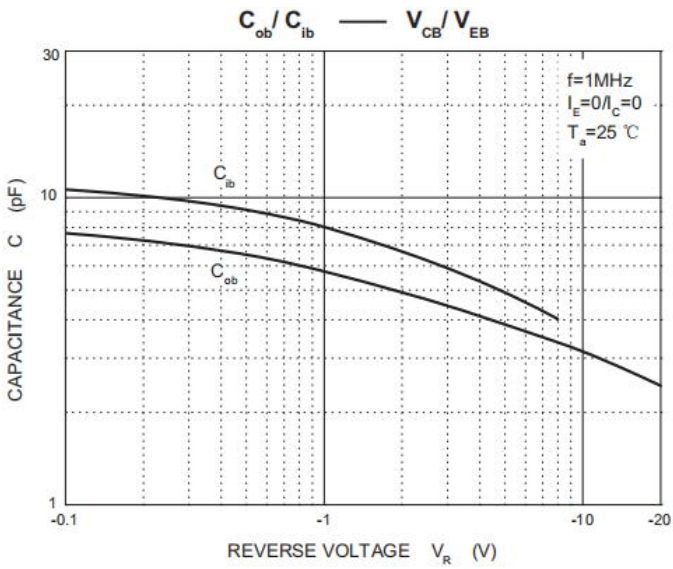
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$			-15	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-15	nA
DC current gain	$h_{FE}$	$V_{CE} = -5V, I_C = -2mA$	110			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -0.5mA$			-0.1	V
		$I_C = -100mA, I_B = -5mA^*$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -0.5mA$		-0.7		V
Output Capacitance	$C_{obo}$	$V_{CB} = -10V, f = 1MHz, I_E = 0$			2.5	pF
Current Gain-Bandwidth product	$f_T$	$V_{CE} = -5V, I_C = -10mA, f = 1MHz$	100			MHz

\*pulse test:  $PW \leq 350\mu S, \delta \leq 2\%$ .

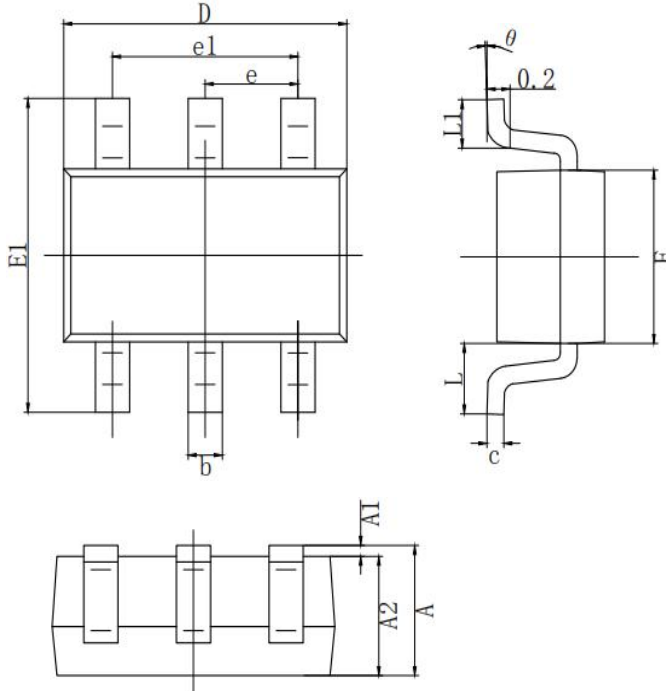
典型特性曲线 Typical Characteristics Curve

Static Characteristic





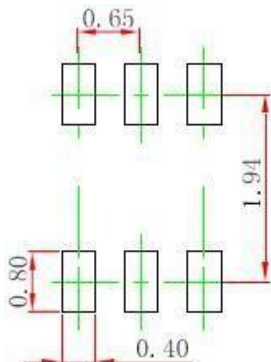
**SOT-363 PACKAGE OUTLINE** Plastic surface mounted package



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
$\theta$	0°	8°

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-363. Electrode patterns for PCBs



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.